



SamHop Microelectronics Corp.



STS3404

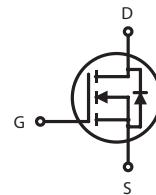
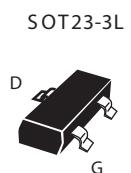
Ver 2.0

## N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
VDSS	ID	RDS(ON) (mΩ) Max
30V	4A	54 @ VGS= 10V
		76 @ VGS= 4.5V

### FEATURES

- Super high dense cell design for low RDS(ON).
- Rugged and reliable.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous <sup>a</sup>	$T_C=25^\circ\text{C}$	A
		$T_C=70^\circ\text{C}$	A
$I_{DM}$	-Pulsed <sup>b</sup>	14	A
$P_D$	Maximum Power Dissipation <sup>a</sup>	$T_C=25^\circ\text{C}$	W
		$T_C=70^\circ\text{C}$	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient <sup>a</sup>	100	$^\circ\text{C/W}$
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## ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V			1	uA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.7	3	V
R <sub>DSON</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =4A		38	54	m ohm
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =3A		55	76	m ohm
g <sub>Fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =4A		8.5		S
<b>DYNAMIC CHARACTERISTICS</b> <sup>c</sup>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V f=1.0MHz		330		pF
C <sub>oss</sub>	Output Capacitance			65		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			50		pF
<b>SWITCHING CHARACTERISTICS</b> <sup>c</sup>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V I <sub>D</sub> =1A V <sub>GS</sub> =10V R <sub>GEN</sub> = 6 ohm		8		ns
t <sub>r</sub>	Rise Time			11		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time			17		ns
t <sub>f</sub>	Fall Time			4		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =4A, V <sub>GS</sub> =10V		7		nC
		V <sub>DS</sub> =15V, I <sub>D</sub> =4A, V <sub>GS</sub> =4.5V		3.5		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =4A, V <sub>GS</sub> =10V		1.2		nC
Q <sub>gd</sub>	Gate-Drain Charge			1.8		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
I <sub>s</sub>	Maximum Continuous Drain-Source Diode Forward Current			1		A
V <sub>SD</sub>	Diode Forward Voltage <sup>b</sup>	V <sub>GS</sub> =0V, I <sub>s</sub> =1A		0.8	1.2	V
<b>Notes</b>						
a.Surface Mounted on FR4 Board,t ≤ 10sec.						
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.						
c.Guaranteed by design, not subject to production testing.						

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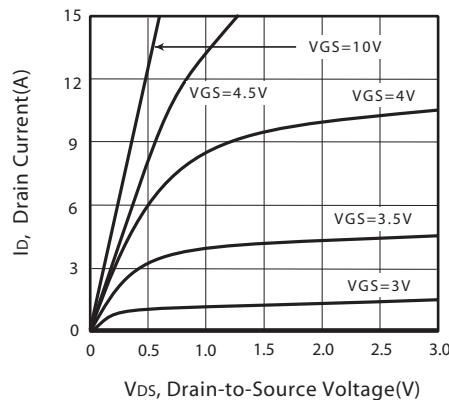


Figure 1. Output Characteristics

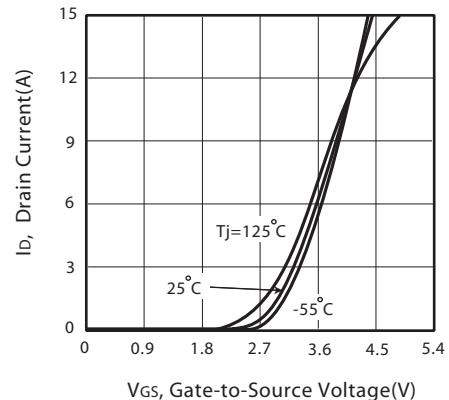


Figure 2. Transfer Characteristics

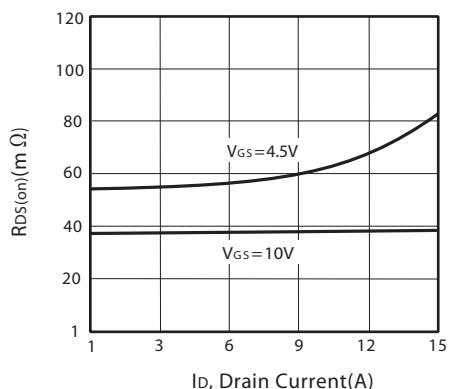


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

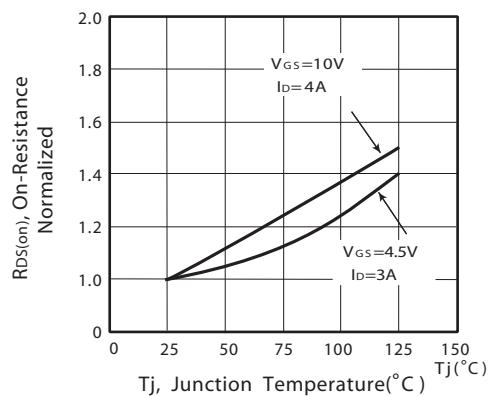


Figure 4. On-Resistance Variation with Drain Current and Temperature

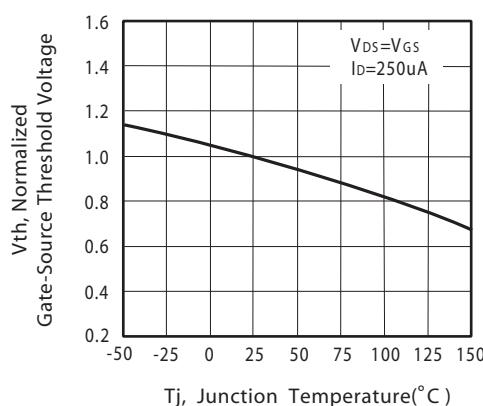


Figure 5. Gate Threshold Variation with Temperature

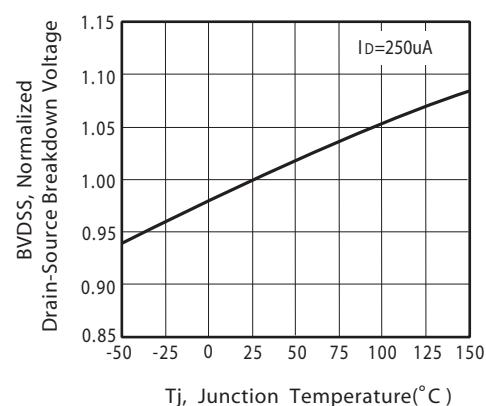


Figure 6. Breakdown Voltage Variation with Temperature

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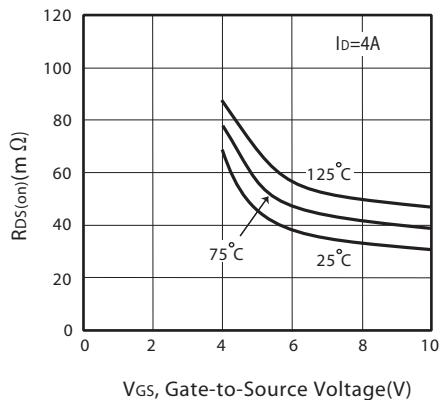


Figure 7. On-Resistance vs. Gate-Source Voltage

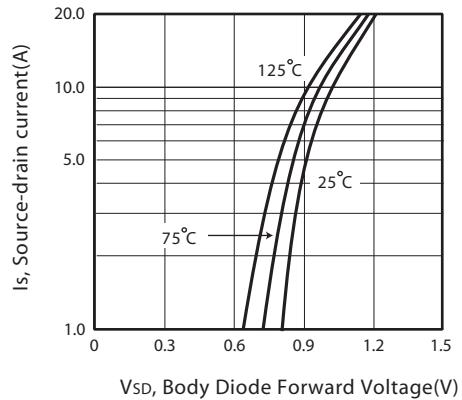


Figure 8. Body Diode Forward Voltage Variation with Source Current

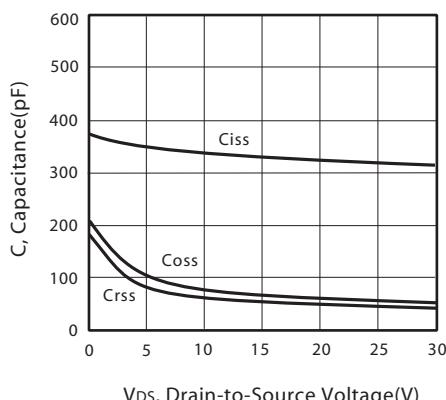


Figure 9. Capacitance

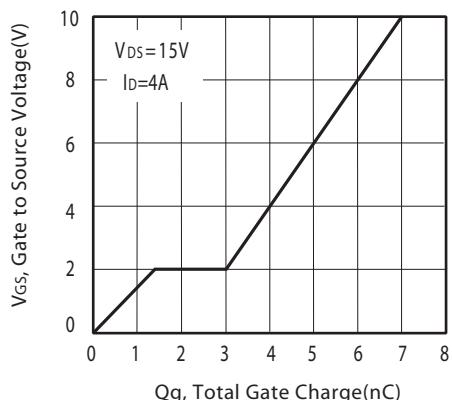


Figure 10. Gate Charge

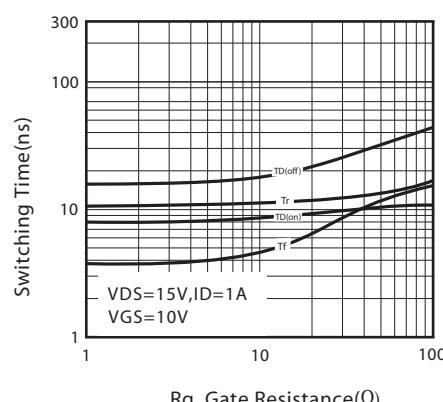


Figure 11. switching characteristics

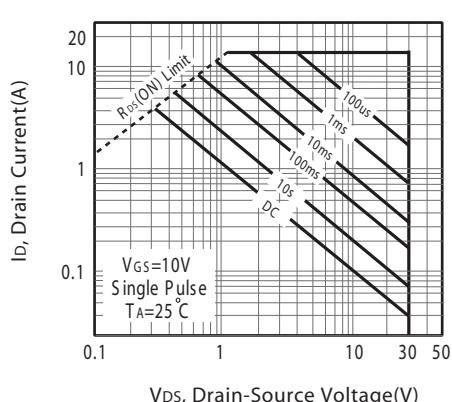


Figure 12. Maximum Safe Operating Area

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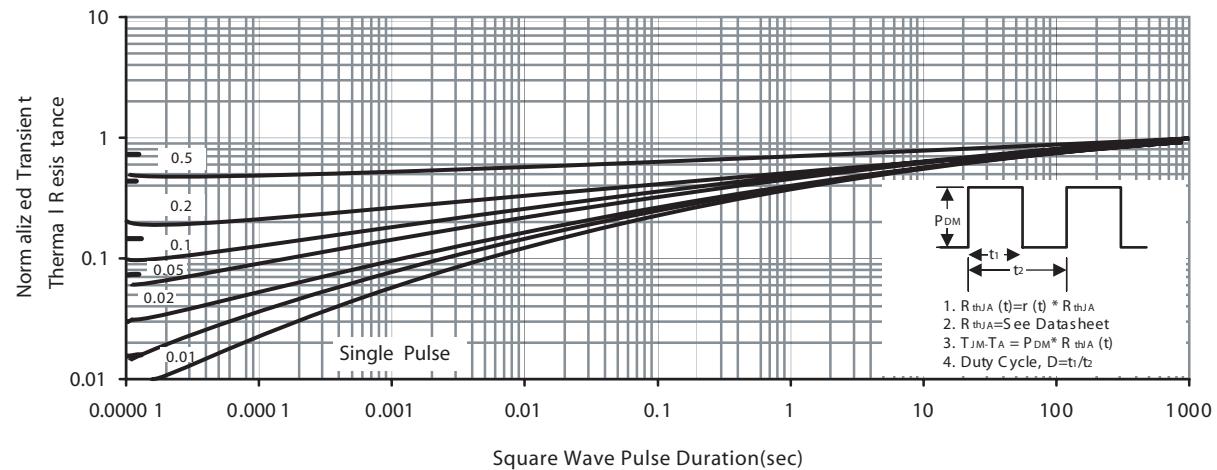
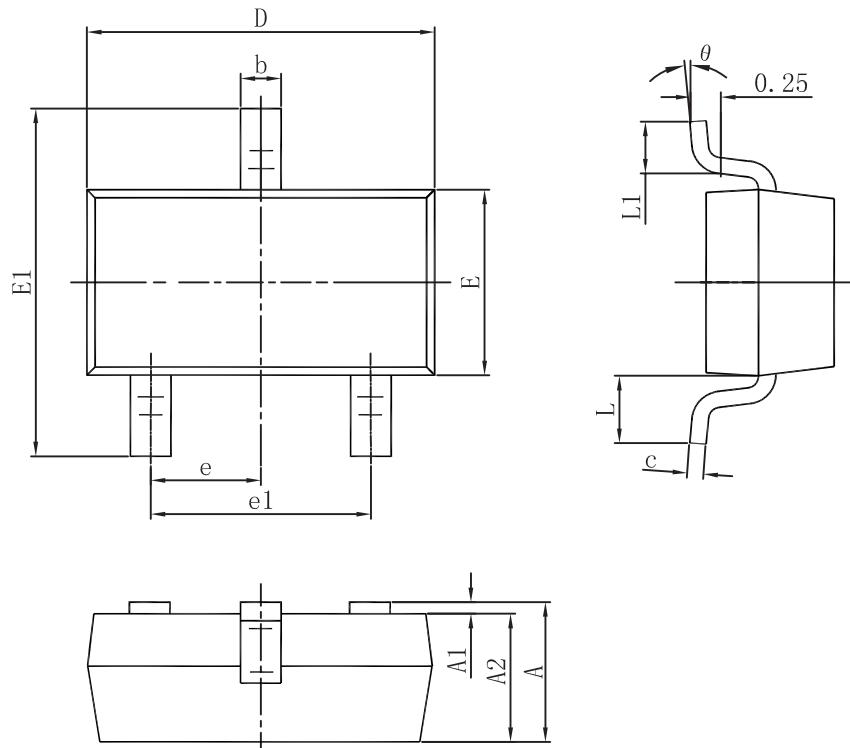


Figure 13. Normalized Thermal Transient Impedance Curve

## PACKAGE OUTLINE DIMENSIONS

### SOT23-3L



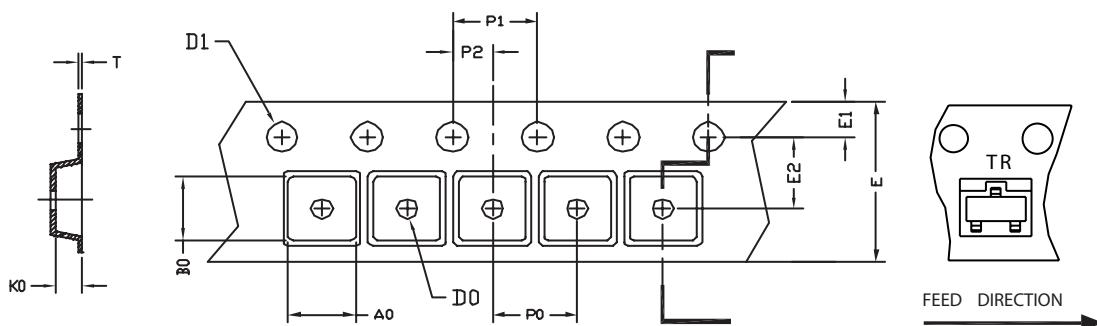
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
	0°	8°	0°	8°

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## SOT23-3L Tape and Reel Data

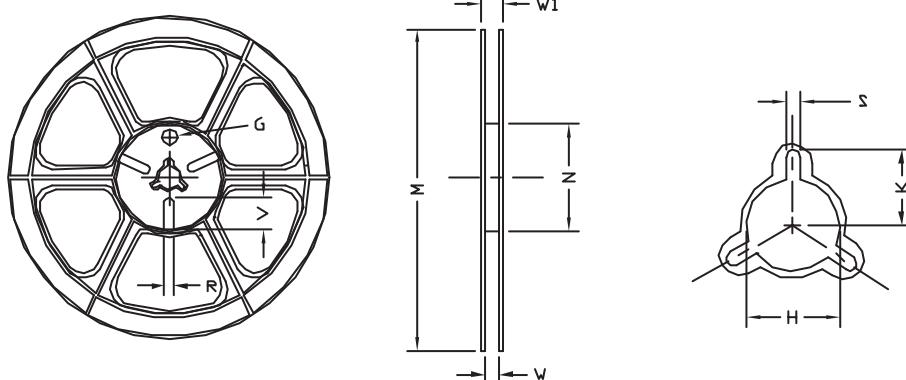
### SOT23-3L Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT23-3L	3.15 ±0.10	2.77 ±0.10	1.22 ±0.10	§ 1.00 +0.05	§ 1.50 +0.10	8.00 +0.30 -0.10	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.22 ±0.04

### SOT23-3L Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	§ 178	§ 178 ±1	§ 60 ±1	9.00 ±0.5	12.00 ±0.5	§ 13.5 ±0.5	10.5	2.00 ±0.5	§ 10.0	5.00	18.00

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